

L Number	Hits	Search Text	DB	Time stamp
1	1048	(SOG) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/25 11:37
2	33	((SOG) and passivation ) and (plan\$10 near passivation)	USPAT	2003/02/25 11:53
3	0	((SOG) and passivation ) and (plan\$10 near passivation)	EPO	2003/02/25 11:54
4	0	((SOG) and passivation ) and (plan\$10 near passivation)	JPO	2003/02/25 11:54
5	0	((SOG) and passivation ) and (plan\$10 near passivation)	DERWENT	2003/02/25 11:54
6	6	((SOG) and passivation ) and (plan\$10 near passivation)	US-PGPUB	2003/02/25 11:55
7	9	((SOG) and passivation ) and (light near shield) and (semiconductor adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/25 11:56

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1	1048	(SOG) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/25 11:37
2	33	((SOG) and passivation ) and (plan\$10 near passivation)	USPAT	2003/02/25 11:53
3	0	((SOG) and passivation ) and (plan\$10 near passivation)	EPO	2003/02/25 11:54
4	0	((SOG) and passivation ) and (plan\$10 near passivation)	JPO	2003/02/25 11:54
5	0	((SOG) and passivation ) and (plan\$10 near passivation)	DERWENT	2003/02/25 11:54
6	6	((SOG) and passivation ) and (plan\$10 near passivation)	US-PGPUB	2003/02/25 11:55
7	9	((SOG) and passivation ) and (light near shield) and (semiconductor adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/25 13:30
8	0	(chemic near2 polishing) and (planar\$ near5 passivation)	USPAT	2003/02/25 13:31
9	0	(chemic near2 polishing) and (planar\$ near5 passivation)	EPO; JPO; DERWENT	2003/02/25 13:31
10	7	(chemical near2 polishing) and (planar\$ near5 passivation)	EPO; JPO; DERWENT	2003/02/25 13:31

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